INTEGRATED CIRCUITS



Product specification Supersedes data of 1996 Sep 10 IC23 Data Handbook

1998 Jan 16



74ABT245

FEATURES

- Octal bidirectional bus interface
- 3-State buffers
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per Jedec Std 17
- ESD protection exceeds 2000 V per MIL STD 833 Method 3015 and 200 V per Machine Model
- Power-up 3-State
- Live insertion/extraction permitted
- Inputs are disabled during 3-State mode

QUICK REFERENCE DATA

DESCRIPTION

The 74ABT245 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

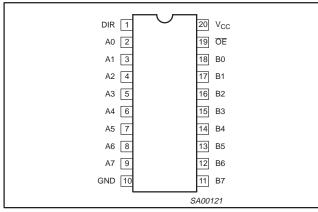
The 74ABT245 device is an octal transceiver featuring non-inverting 3-State bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an Output Enable (\overline{OE}) input for easy cascading and a Direction (DIR) input for direction control.

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	C _L = 50pF; V _{CC} = 5V	2.2 2.9	ns
C _{IN}	Input capacitance DIR, OE	$V_{I} = 0V \text{ or } V_{CC}$	4	pF
C _{I/O}	I/O pin capacitance	Outputs disabled; $V_0 = 0V$ or V_{CC}	7	pF
I _{CCZ}	Total supply current	Outputs disabled; V _{CC} =5.5V	50	μΑ

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
20-Pin Plastic DIP	–40°C to +85°C	74ABT245 N	74ABT245 N	SOT146-1
20-Pin plastic SO	–40°C to +85°C	74ABT245 D	74ABT245 D	SOT163-1
20-Pin Plastic SSOP Type II	–40°C to +85°C	74ABT245 DB	74ABT245 DB	SOT339-1
20-Pin Plastic TSSOP Type I	–40°C to +85°C	74ABT245 PW	74ABT245PW DH	SOT360-1

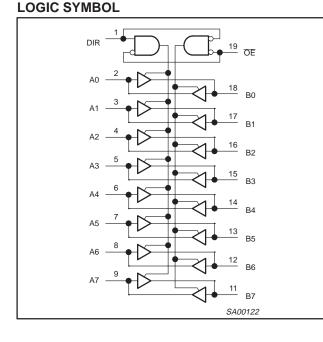
PIN CONFIGURATION



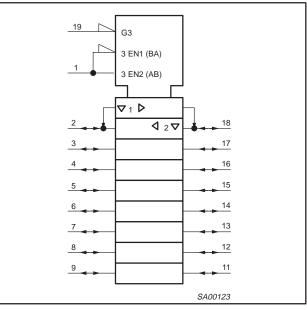
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1	DIR	Direction control input
2, 3, 4, 5, 6, 7, 8, 9	A0 – A7	Data inputs/outputs (A side)
18, 17, 16, 15, 14, 13, 12, 11	B0 – B7	Data inputs/outputs (B side)
19	ŌĒ	Output enable input (active-Low)
10	GND	Ground (0V)
20	V _{CC}	Positive supply voltage

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LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INP	JTS	INPUTS/C	OUTPUTS
ŌĒ	DIR	An	Bn
L	L	An = Bn	Inputs
L	Н	Inputs	Bn = An
н	Х	Z	Z

H = High voltage level

L = Low voltage level

X = Don't care Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current	V ₁ < 0	-18	mA
VI	DC input voltage ³		-1.2 to +7.0	V
I _{ОК}	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I _{OUT}	DC output current	output in Low state	128	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	ITS	UNIT
STWBOL	PARAMETER	Min	Max	UNIT
V _{CC}	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V _{CC}	V
V _{IH}	High-level input voltage	2.0		V
VIL	Low-level Input voltage		0.8	V
I _{ОН}	High-level output current		-32	mA
I _{OL}	Low-level output current		64	mA
Δt/Δv	Input transition rise or fall rate	0	5	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS

						LIMITS			
SYMBOL	PARAM	ETER	TEST CONDITIONS	Ta	_{mb} = +25	°C	T _{amb} =	–40°C 85°C	UNIT
				Min	Тур	Max	Min	Max	
V _{IK}	Input clamp volt	age	$V_{CC} = 4.5V; I_{IK} = -18mA$		-0.9	-1.2		-1.2	V
			V_{CC} = 4.5V; I_{OH} = –3mA; V_{I} = V_{IL} or V_{IH}	2.5	2.9		2.5		V
V _{OH}	High-level outpu	ut voltage	V_{CC} = 5.0V; I_{OH} = -3mA; V_I = V_{IL} or V_{IH}	3.0	3.4		3.0		V
			V_{CC} = 4.5V; I_{OH} = -32mA; V_I = V_{IL} or V_{IH}	2.0	2.4		2.0		V
V _{OL}	Low-level output	t voltage	V_{CC} = 4.5V; I_{OL} = 64mA; V_I = V_{IL} or V_{IH}		0.42	0.55		0.55	V
lı lı	Input leakage	Control pins	$V_{CC} = 5.5V; V_{I} = GND \text{ or } 5.5V$		±0.01	±1.0		±1.0	μΑ
	current	Data pins	V_{CC} = 5.5V; V_I = GND or 5.5V		±5	±100		±100	μΑ
I _{OFF}	Power-off leaka	ge current	V_{CC} = 0.0V; V _I or V _O \leq 4.5V		±5.0	±100		±100	μΑ
I _{PU} /I _{PD}	Power-up/down 3-State output current ³		V_{CC} = 2.0V; V_{O} = 0.5V; V_{I} = GND or V_{CC} ; V_{OE} = Don't care		±5.0	±50		±50	μA
I _{IH} + I _{OZH}	3-State output H	ligh current	V_{CC} = 5.5V; V_{O} = 2.7V; V_{I} = V_{IL} or V_{IH}		5.0	50		50	μΑ
I _{IL} + I _{OZL}	3-State output L	ow current	V_{CC} = 5.5V; V_{O} = 0.5V; V_{I} = V_{IL} or V_{IH}		-5.0	-50		-50	μΑ
I _{CEX}	Output high leal	kage current	V_{CC} = 5.5V; V_{O} = 5.5V; V_{I} = GND or V_{CC}		5.0	50		50	μΑ
Ι _Ο	Output current ¹		V _{CC} = 5.5V; V _O = 2.5V	-40	-100	-180	-40	-180	mA
I _{CCH}			V_{CC} = 5.5V; Outputs High, V_{I} = GND or V_{CC}		50	250		250	μΑ
I _{CCL}	Quiescent supp	ly current	V_{CC} = 5.5V; Outputs Low, V_{I} = GND or V_{CC}		24	30		30	mA
I _{CCZ}			V_{CC} = 5.5V; Outputs 3-State; V _I = GND or V _{CC}		50	250		250	μΑ
			Outputs enabled, one input at 3.4V, other inputs at V _{CC} or GND; V _{CC} = 5.5V		0.5	1.5		1.5	mA
ΔI _{CC}	Additional supp input pin ²	y current per	Outputs 3-State, one data input at 3.4V, other inputs at V_{CC} or GND; V_{CC} = 5.5V		50	250		250	μΑ
			Outputs 3-State, one enable input at 3.4V, other inputs at V _{CC} or GND; V_{CC} = 5.5V		0.5	1.5		1.5	mA

NOTES:

Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
This is the increase in supply current for each input at 3.4V.
This parameter is valid for any V_{CC} between 0V and 2.1V with a transition time of up to 10msec. For V_{CC} = 2.1V to V_{CC} = 5V±10%, a transition time of up to 100µsec is permitted.

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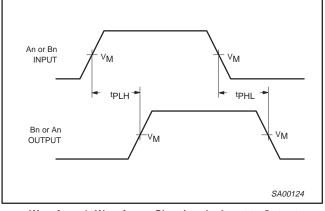
AC CHARACTERISTICS

GND = 0V; $t_R = t_F = 2.5 \text{ns}$; $C_L = 50 \text{pF}$, $R_L = 500 \Omega$

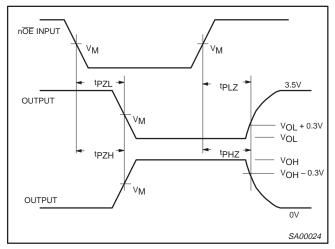
SYMBOL	PARAMETER	WAVEFORM	T _a V	_{mb} = +25° _{CC} = +5.0	C V	$T_{amb} = -40^{\circ}$ $V_{CC} = +5.$	UNIT	
			Min	Тур	Мах	Min	Max	
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	1	1.0 1.0	2.2 2.9	4.1 4.2	1.0 1.0	4.6 4.6	ns
t _{PZH} t _{PZL}	Output enable time to High and Low level	2	1.3 2.3	3.0 4.0	4.8 5.8	1.3 2.3	5.3 6.3	ns
t _{PHZ} t _{PLZ}	Output disable time from High and Low Level	2	1.0 1.0	4.7 4.1	6.2 5.8	1.0 1.0	7.2 6.3	ns

AC WAVEFORMS

 V_{M} = 1.5V, V_{IN} = GND to 3.0V

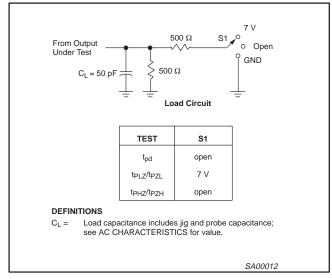


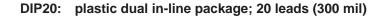
Waveform 1. Waveforms Showing the Input to Output Propagation Delays

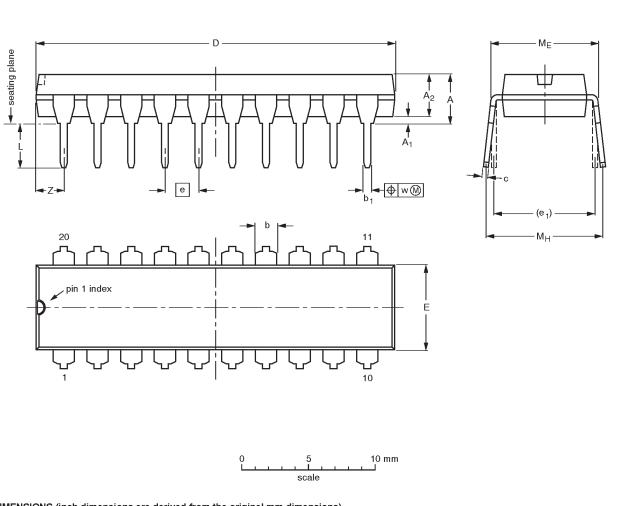


Waveform 2. Waveforms Showing the 3-State Output Enable and Disable Times

TEST CIRCUIT AND WAVEFORMS







DIMENSIC	n aimens	ions are	aerivea t	rom the c	original n	nm aimei	nsions)	
					1			

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.0
inches	0.17	0.020	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEDEC EIAJ		PROJECTION	ISSUE DATE	
SOT146-1			SC603			-92-11-17- 95-05-24	

Product specification 74ABT245

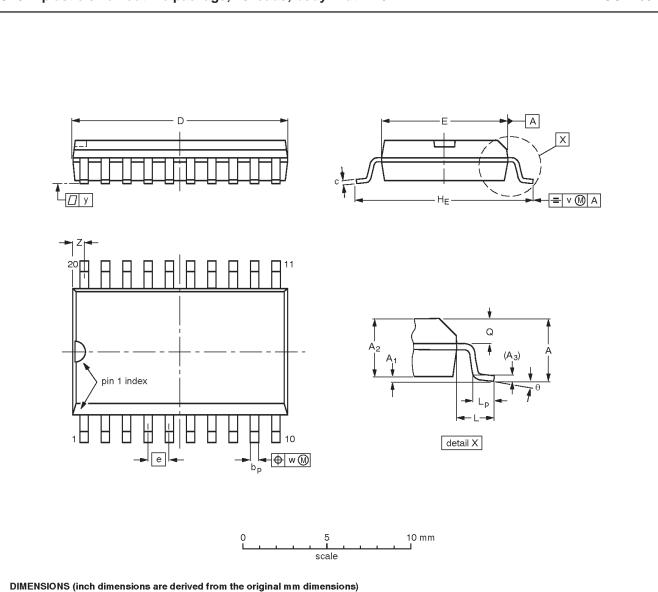
SOT146-1

Product specification

74ABT245

Octal transceiver with direction pin (3-State)

SO20: plastic small outline package; 20 leads; body width 7.5 mm



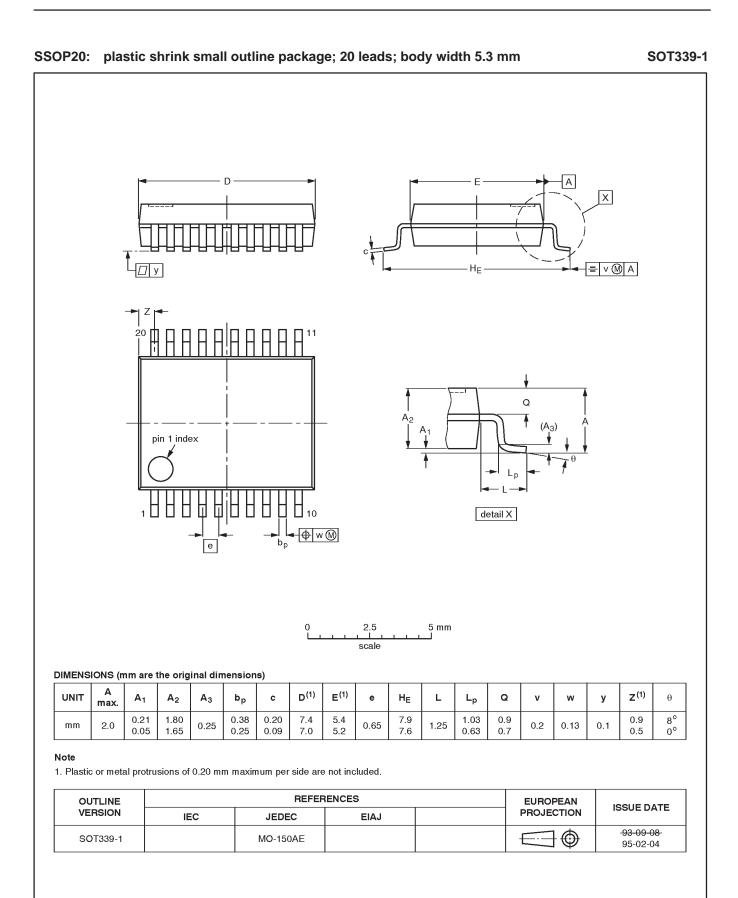
UNIT	A max.	A ₁	A ₂	A ₃	bp	с	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	2.65	0.30 0.10	2.45 2.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.10	0.012 0.004	0.096 0.089	0.01	0.019 0.014		0.51 0.49	0.30 0.29	0.050	0.42 0.39	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

Note

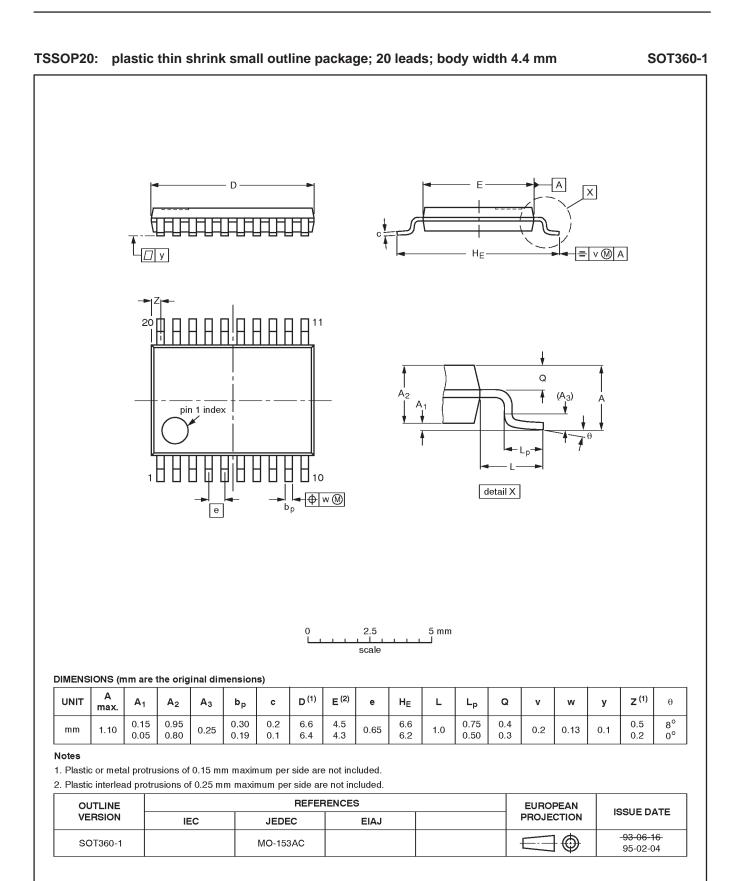
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT163-1	075E04	MS-013AC				-92-11-17 95-01-24

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Data sheet status

Data sheet status	Product status	Definition [1]	
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.	
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later da Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.	
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible produ	

[1] Please consult the most recently issued datasheet before initiating or completing a design.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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